

Reviving Moore's Law with an EUV FEL

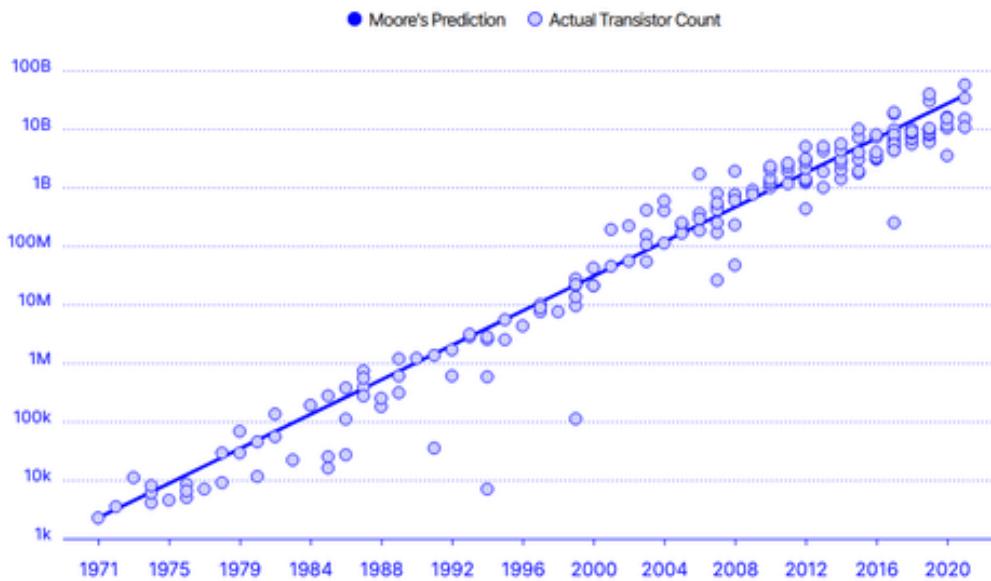
Nicholas Kelez



What is Moore's Law?

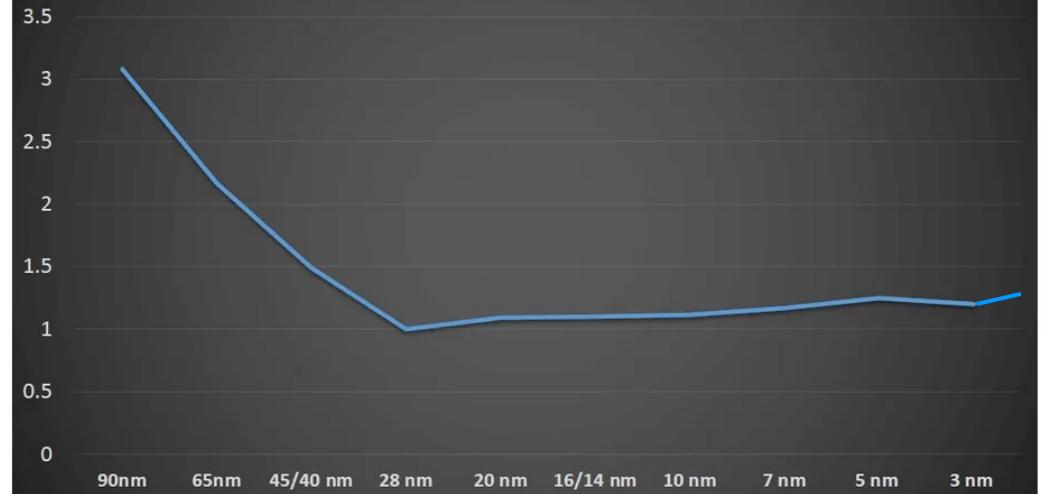
Moore's Law

"The number of transistors in a dense integrated circuit (IC) doubles about every two years."



Transistor Cost Trend

Cost of 100M Gates Normalized to 28nm

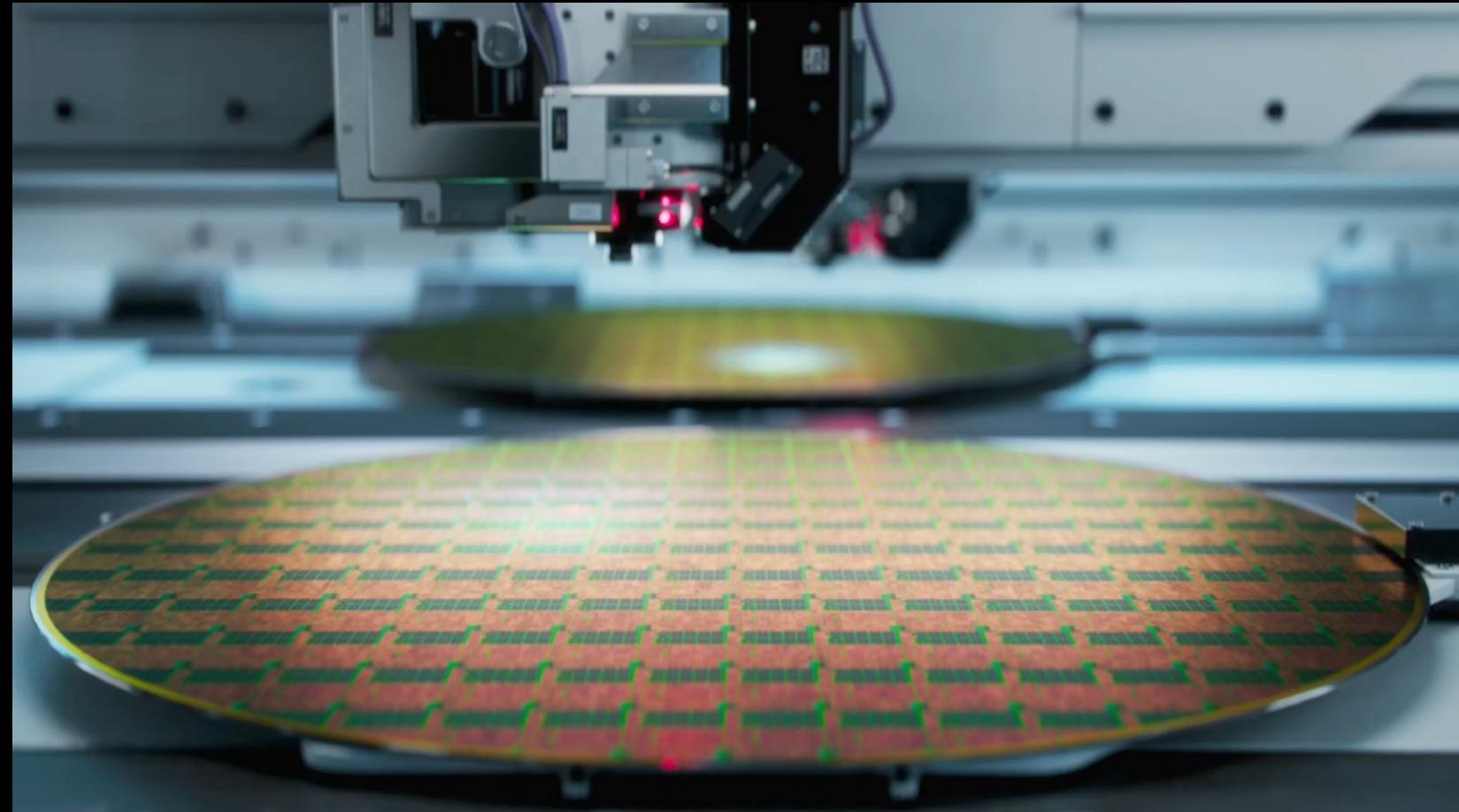


- Transistor cost scaling (0.7X) stalled at 28 nm and remains flat gen over gen

Transforming Semiconductor Manufacturing

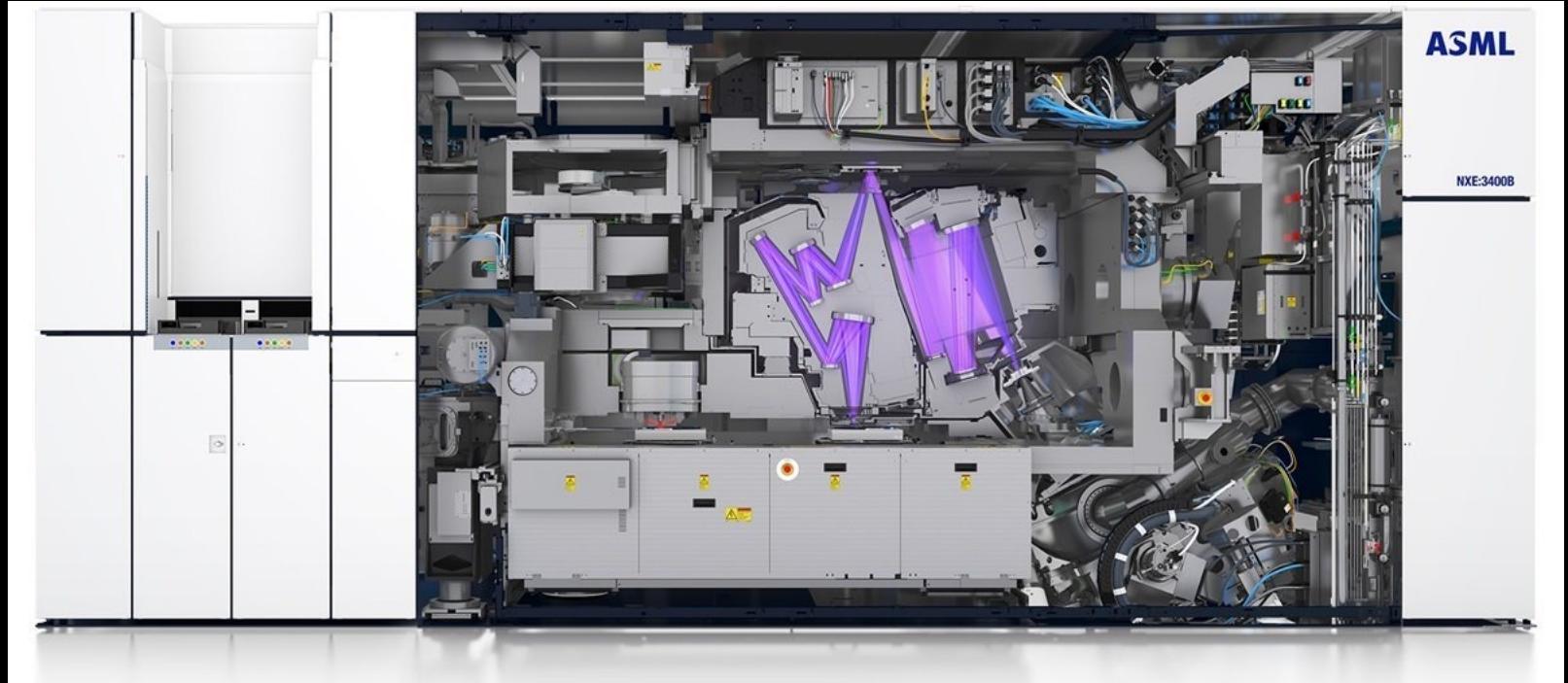
EUV FEL makes advanced chip manufacturing:

- Better
- Faster
- Cheaper
- More efficient



Delivering Unlimited Light

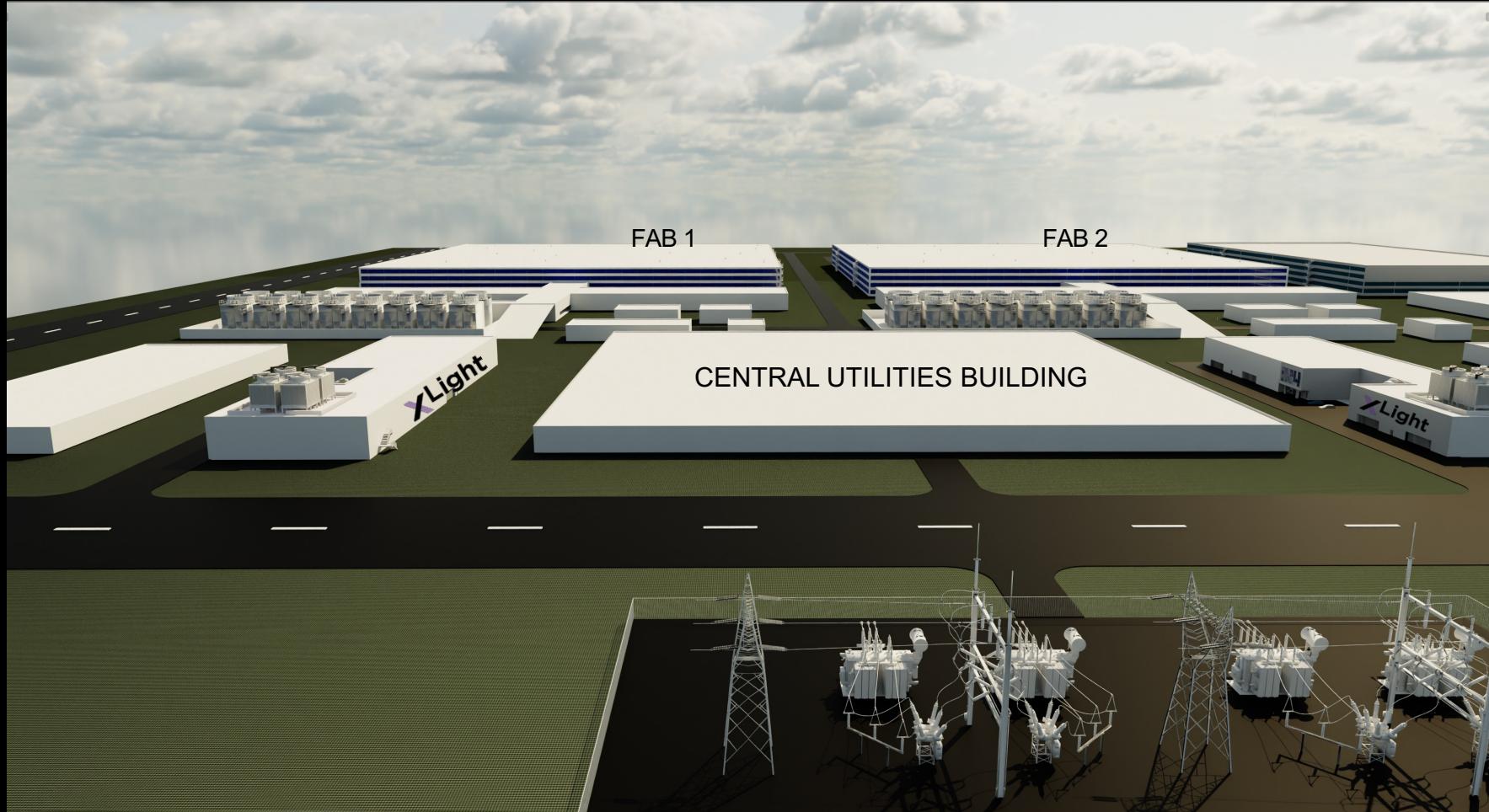
Partner with ASML
to unlock capabilities
and enable future
advancements



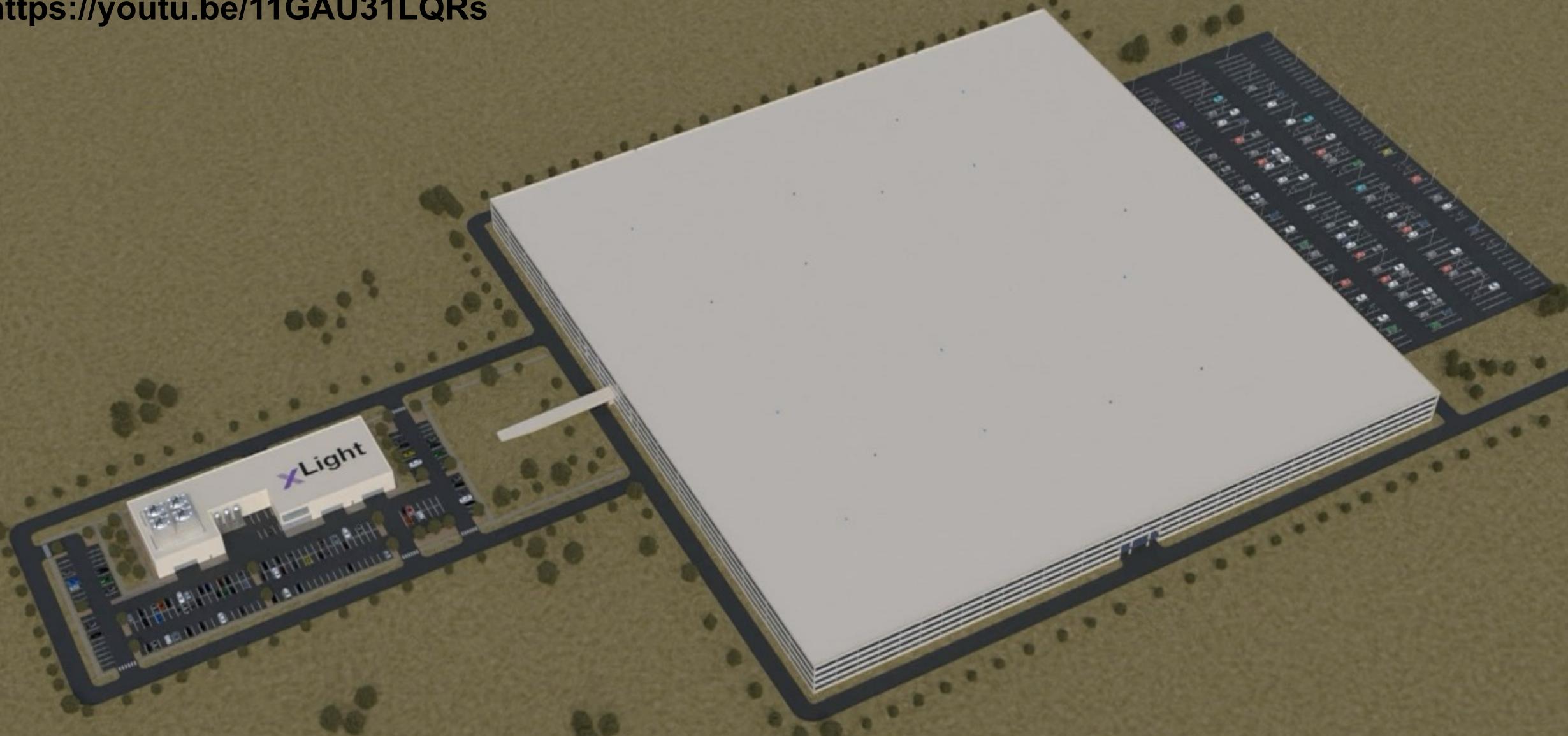
EUV LITHOGRAPHY

Building Utility-Scale Systems

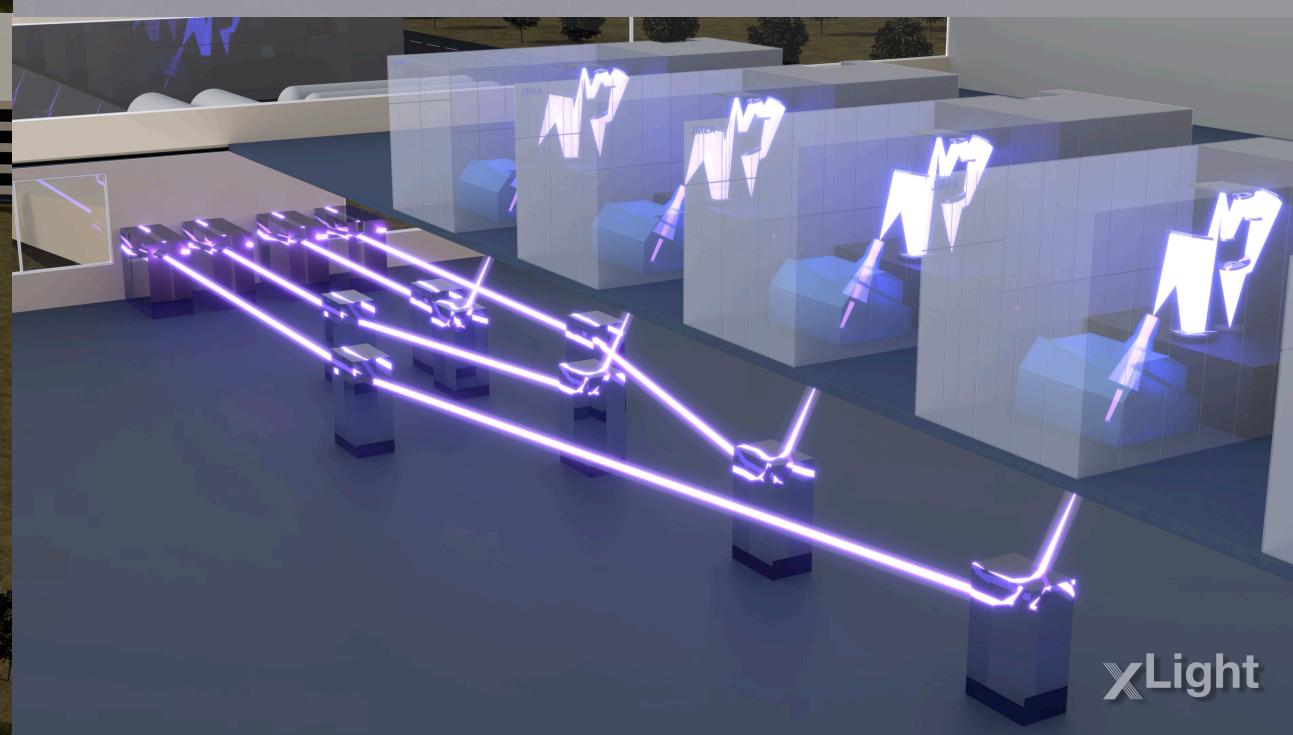
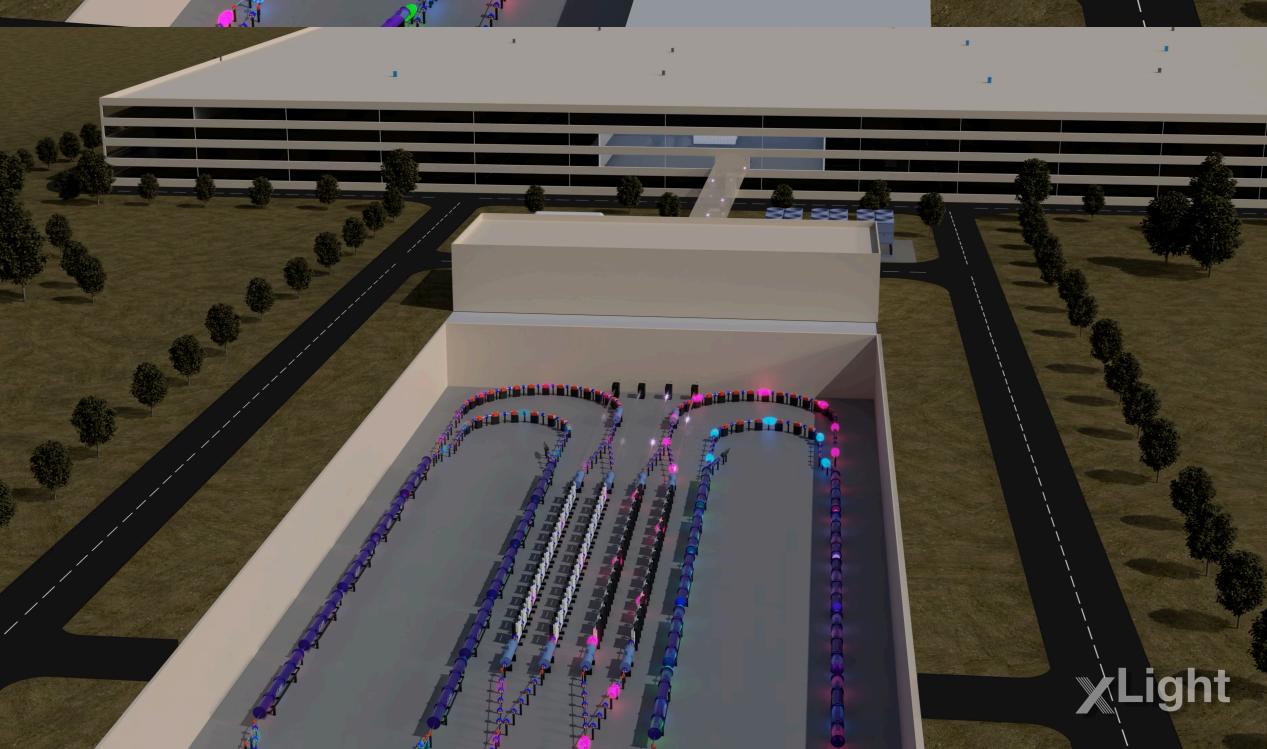
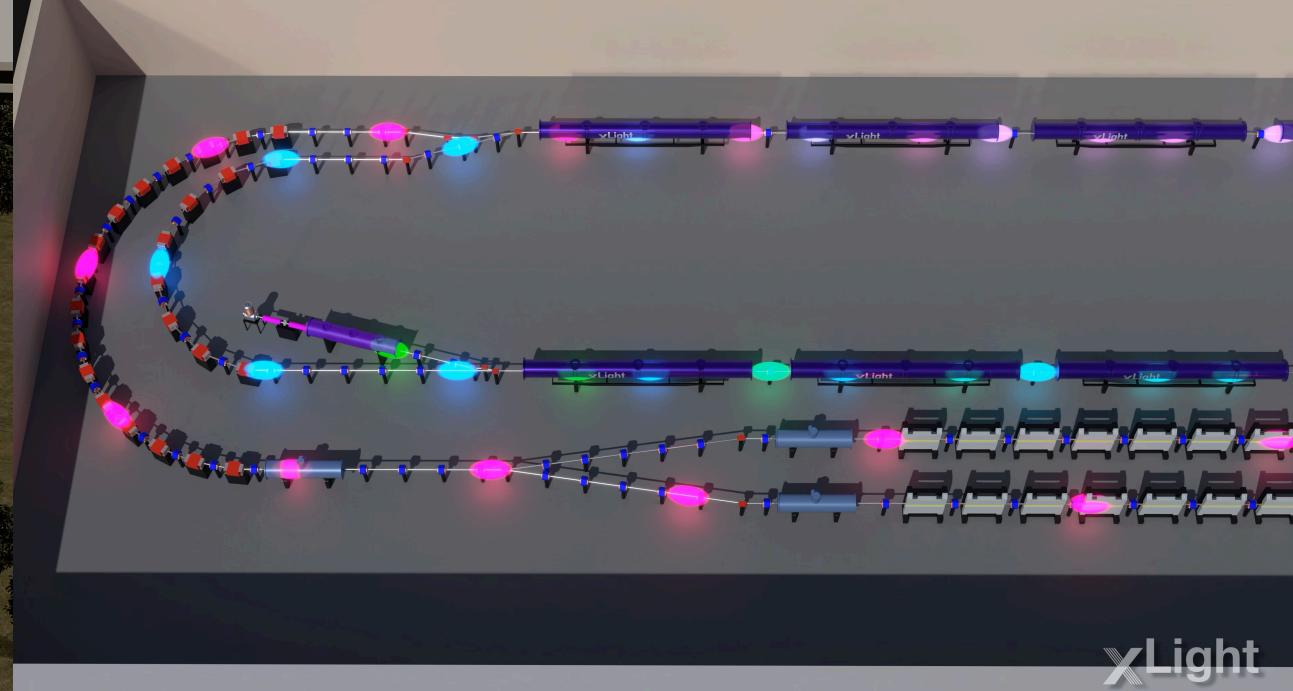
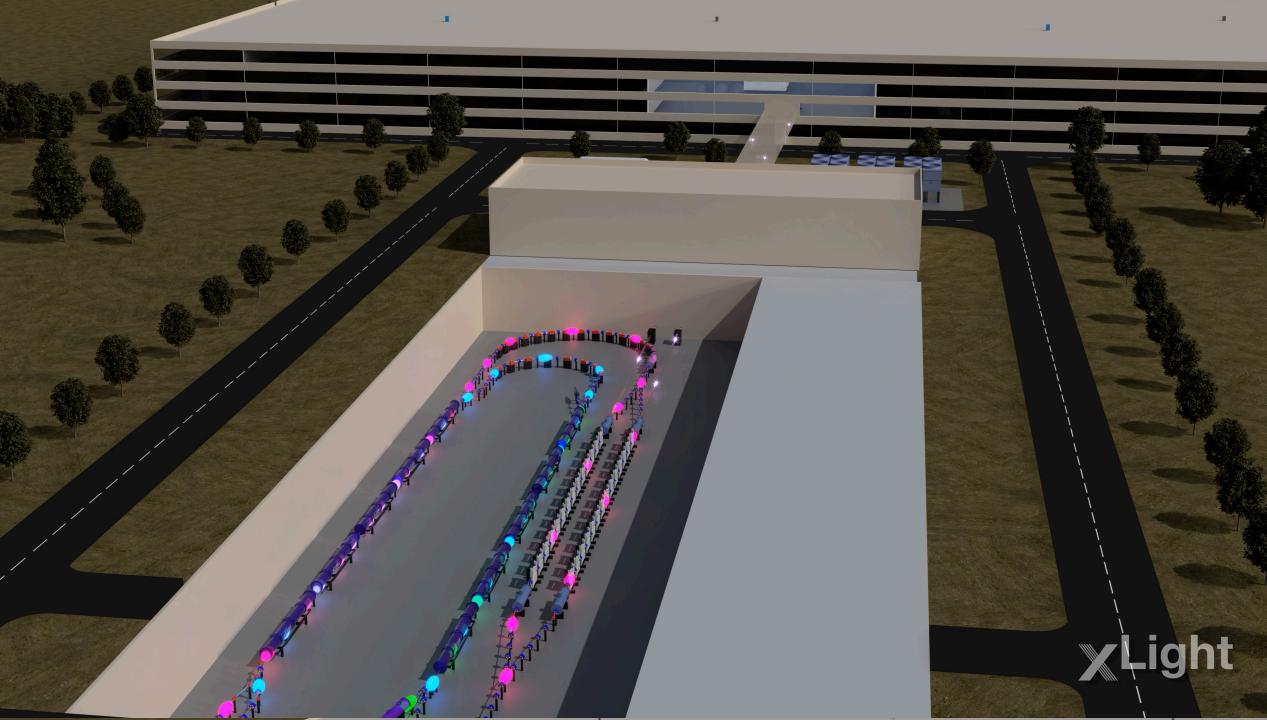
- More power
- Tunable platform
- Light as a Service (LaaS)



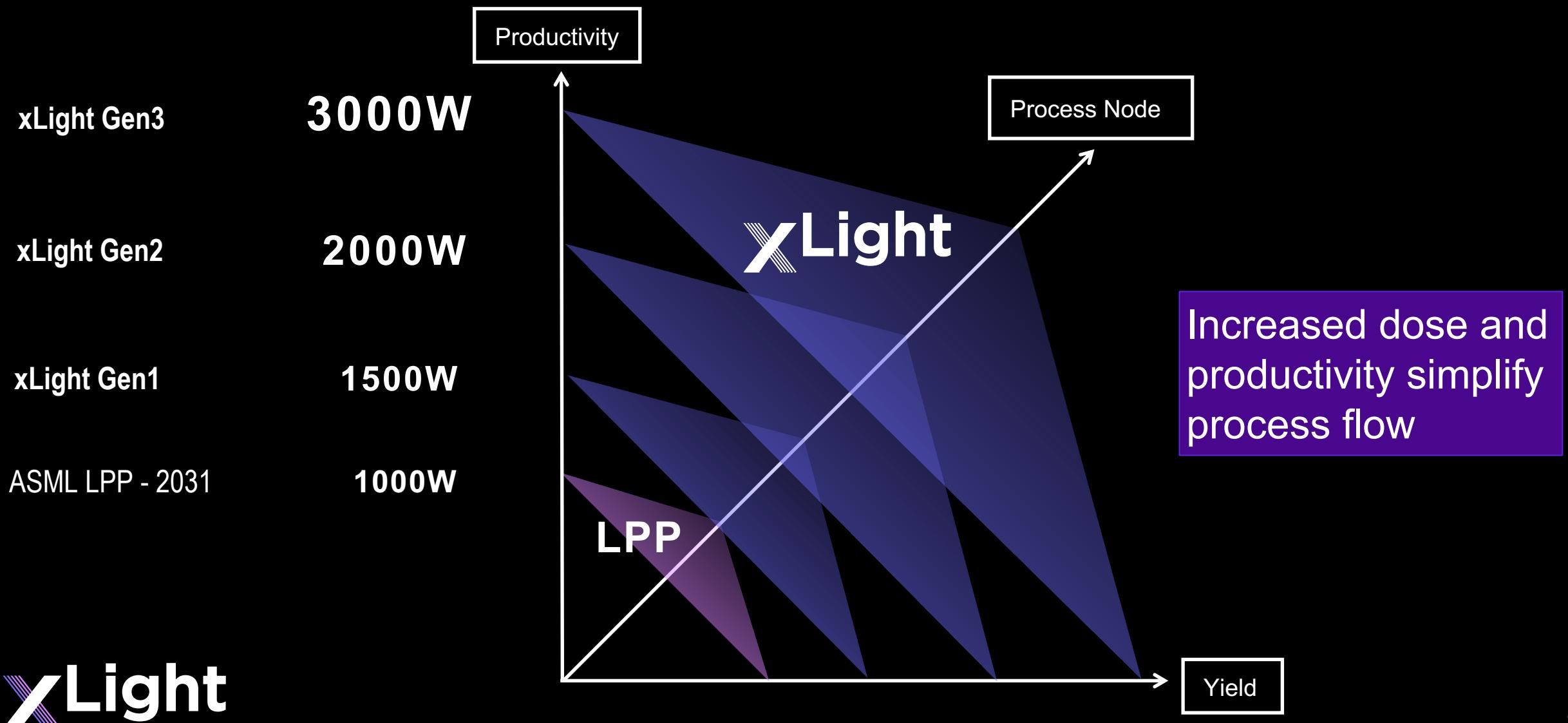
<https://youtu.be/11GAU31LQRs>



xLight

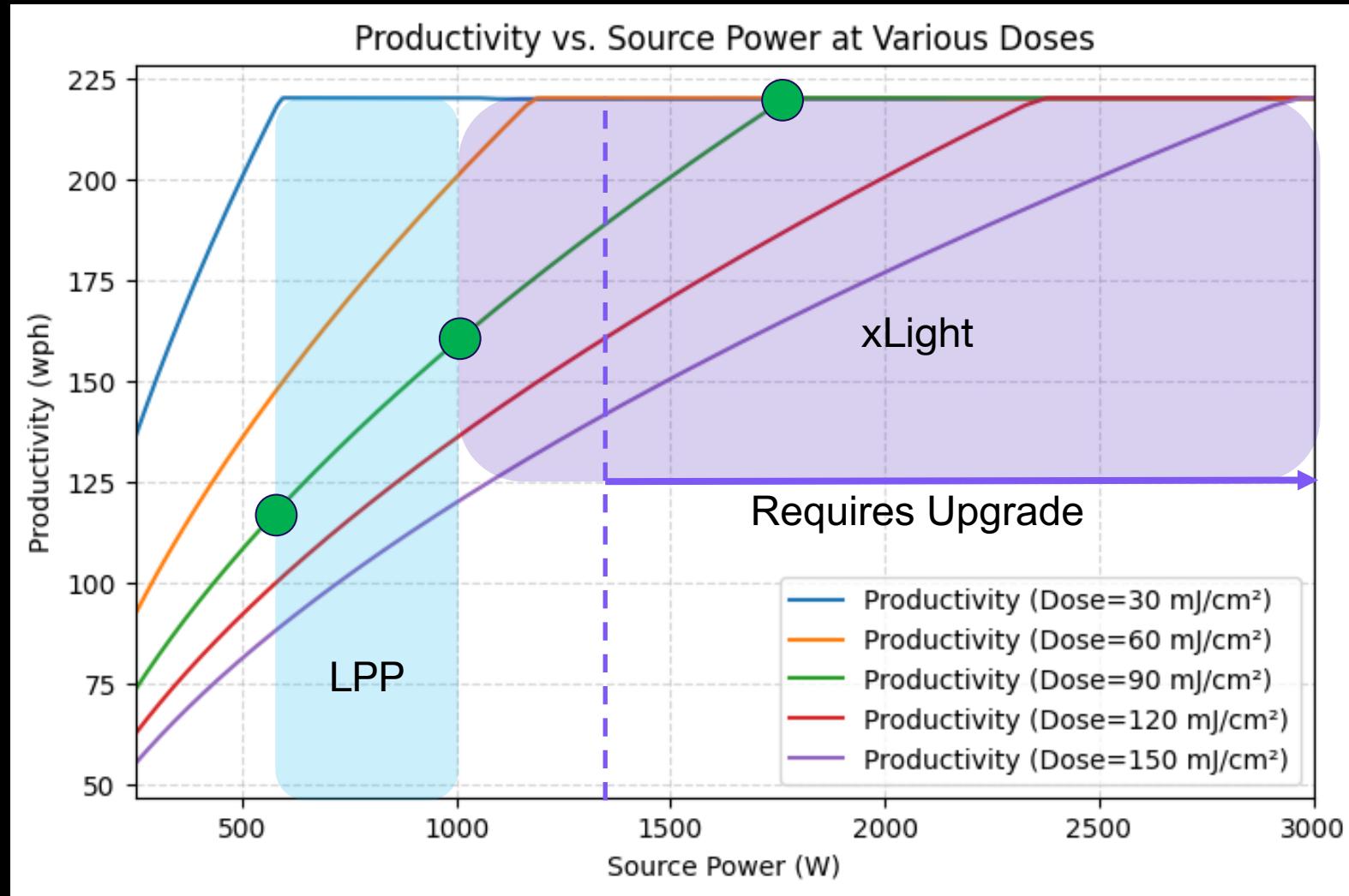


Power Unlocks Performance, Productivity, & Yield



xLight

Source Power Drives Productivity



Dose Scales with Critical Dimension

Reduction in Feature Size Drives Resist Dose Increases

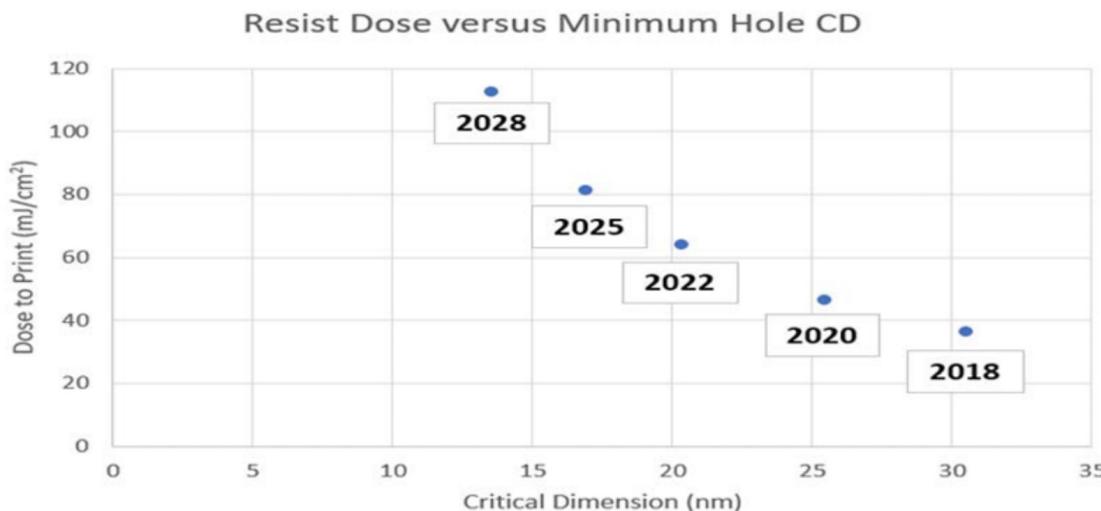


Figure LITH-1 2020 Projected EUV Photo-Speed as a Function of Printed Contact Hole Size

IDRS 2020 Lithography Roadmap predicts rise in dose requirements due to more demanding LCDU requirements as as feature sizes get smaller.

https://irds.ieee.org/images/files/pdf/2020/2020IRDS_Litho.pdf

$$Dose = \frac{576}{\alpha d} \frac{h\nu}{f^2 CD^2 NILS^2}$$

Geh equation predicts that doses for equivalent LCDU will have to increase as $1/CD^2$

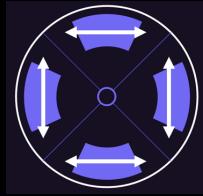
Doses at 14 nm will be 5x higher than doses at 32 nm.

More about that in a future talk!

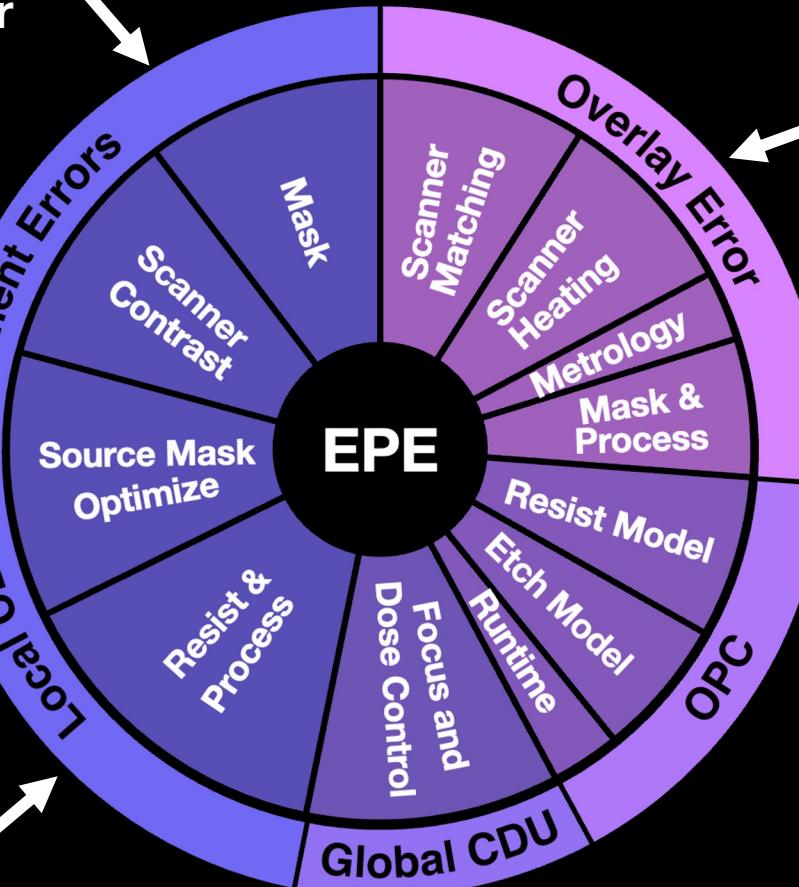
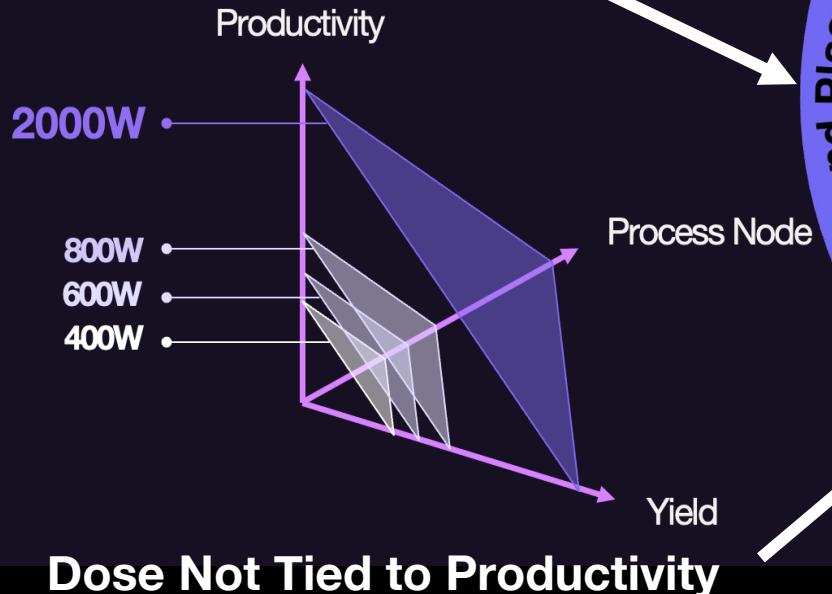


Better Patterning with an EUV FEL

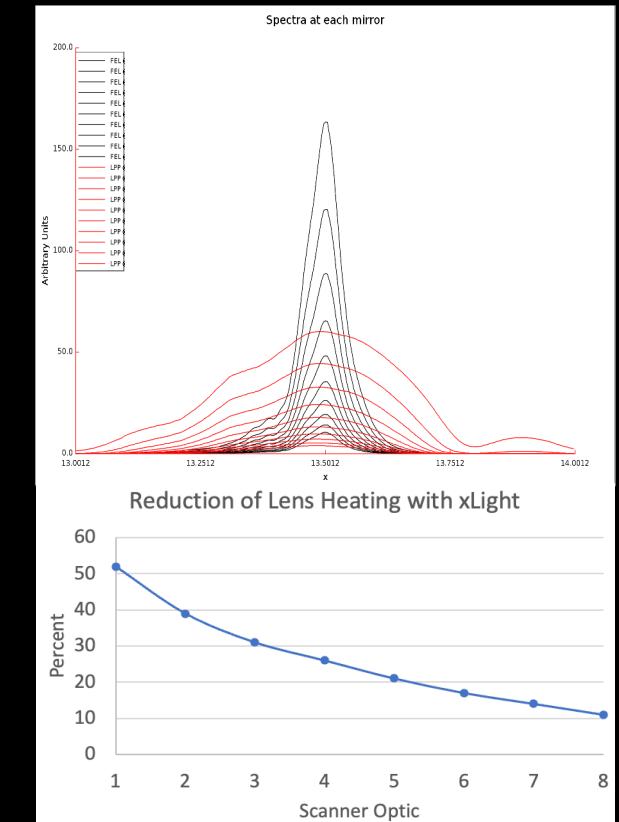
Power + Polarization Trade
for Improved Angular
Bandwidth



Zone Polarization



EPE budget recreated from ASML public data.



Tunable Source Enables Next Generation Lithography

$$\text{Critical Dimension (CD)} = k_1 \times \lambda / \text{NA}$$

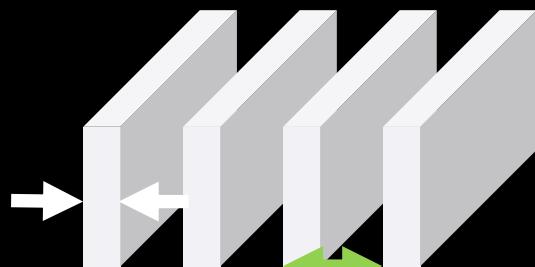
Current 13.5nm



9.5nm / 29nm

k_1 reduction:
Polarization

13.5nm w/ xLight



6.8nm / 22nm

40% Area
Scaling

Future 4.5nm w/ xLight



3.2nm / 10nm

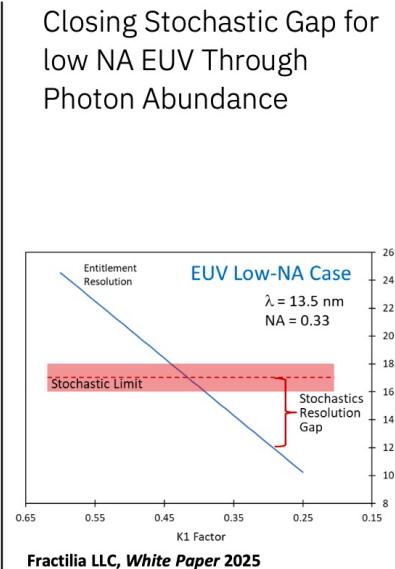
80% Area
Scaling

FEL enables generations of cost and performance scaling

$$LER \propto \frac{1}{\sqrt{N}} \times \frac{1}{ILS}$$

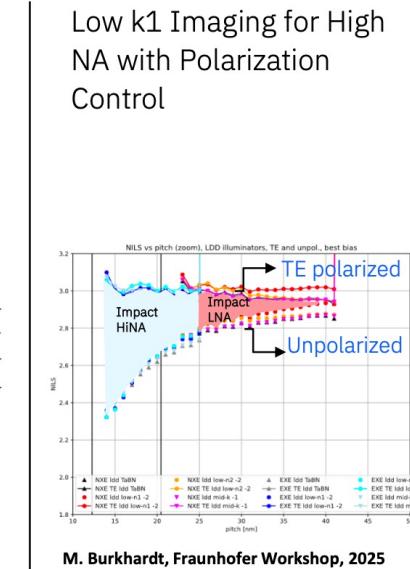
Source:
IBM Research
SPIE EUVLitho
Sept 22, 2025

FEL source enablement for EPE control: aligning scaling needs with productivity goals



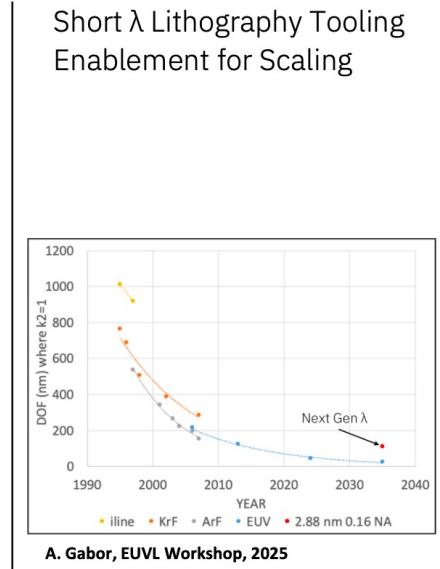
Now

Closing Stochastic Gap for low NA EUV Through Photon Abundance



Next

Low k_1 Imaging for High NA with Polarization Control

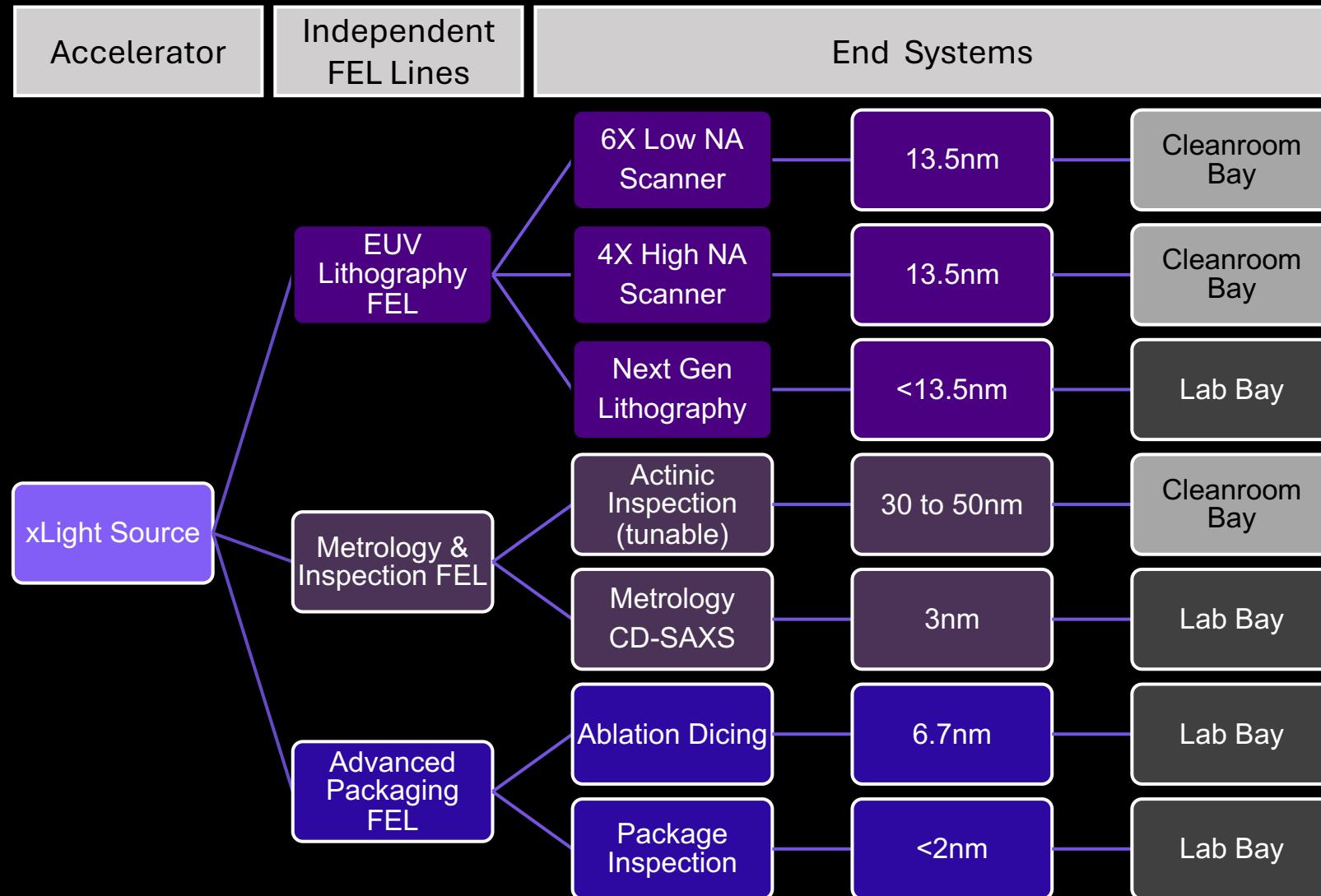


Future

Short λ Lithography Tooling Enablement for Scaling

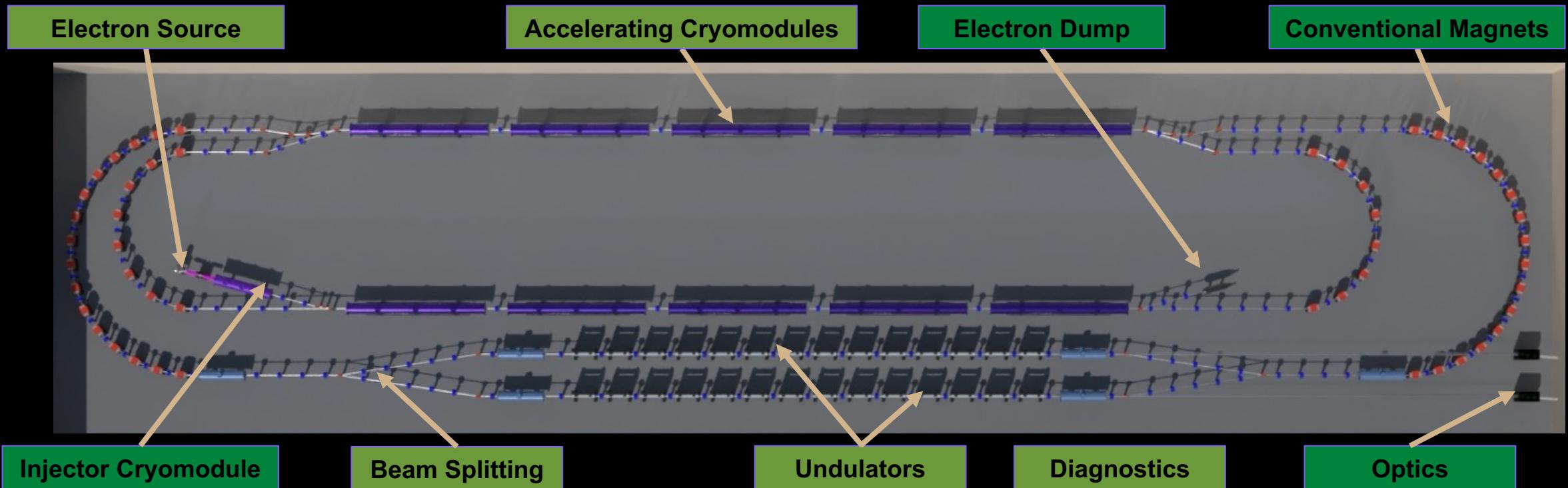
	Nominal	Enable single-exposure at max tpt	Comparison
28nm pitch line/space	2x Low-NA EUV LELE	1x Low-NA EUV with high-dose but max tpt	Reduce cost of module by 36% (stochastics improvement)
21nm pitch line/space	3x Low-NA EUV SALELE	1x High-NA EUV with high-dose but max tpt	Module cost 2x cheaper (previously 1.7x cheaper)
21nm pitch line/space	1x High-NA EUV	1x High-NA EUV with high-dose but max tpt	Reduce exposure cost by 40%
16nm pitch line/space	2x High-NA EUV LELE	1x High-NA EUV with high-dose but max tpt	Module cost 2x cheaper (resolution improvement)

One Light Source Enables an Ecosystem



Lab to Fab - New Applications of Proven Technologies

Building prototypes & first articles now



Argonne
NATIONAL LABORATORY



xLight



Fermilab

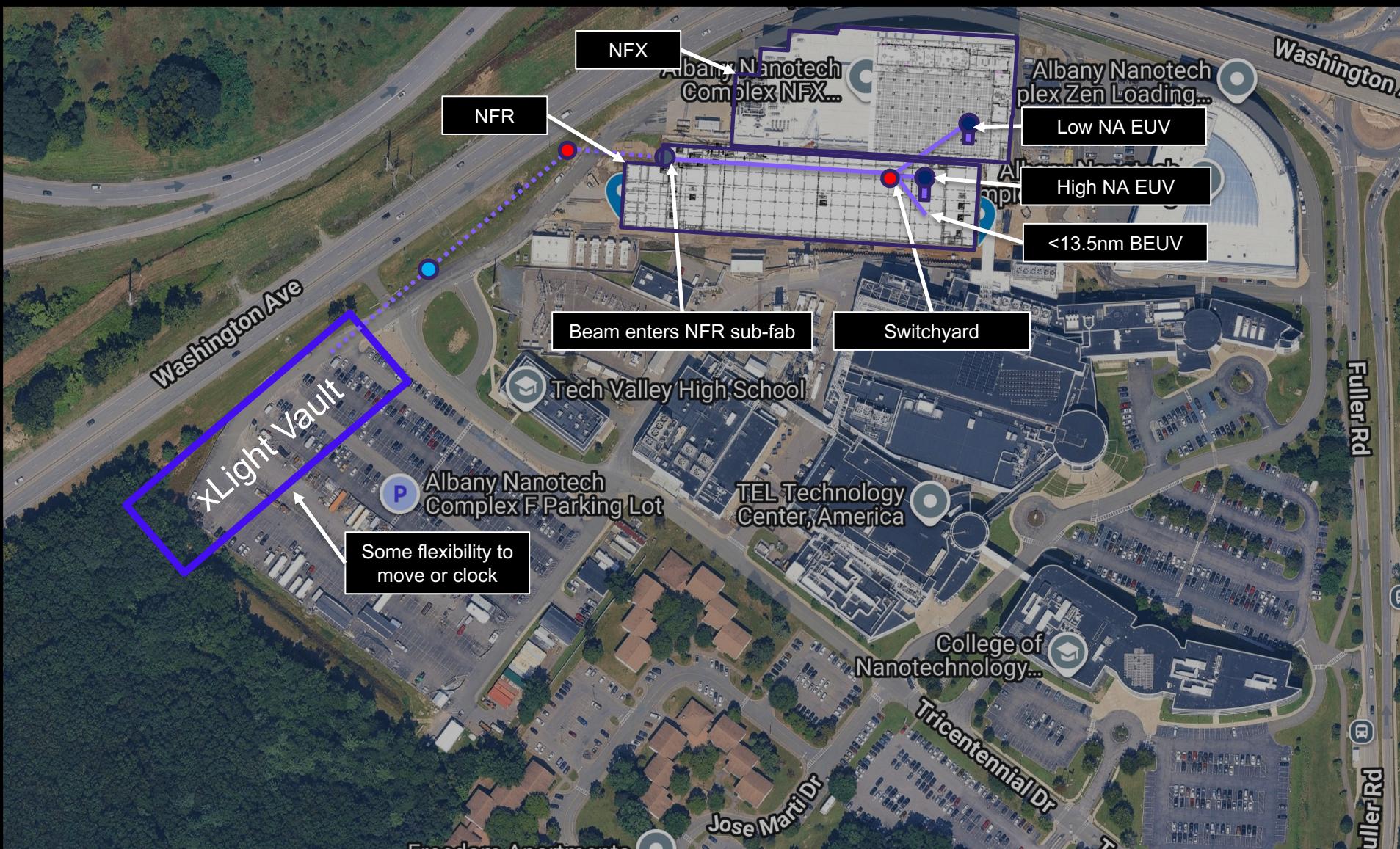
Jefferson
Lab

Los Alamos
NATIONAL LABORATORY

OAK
RIDGE
National Laboratory

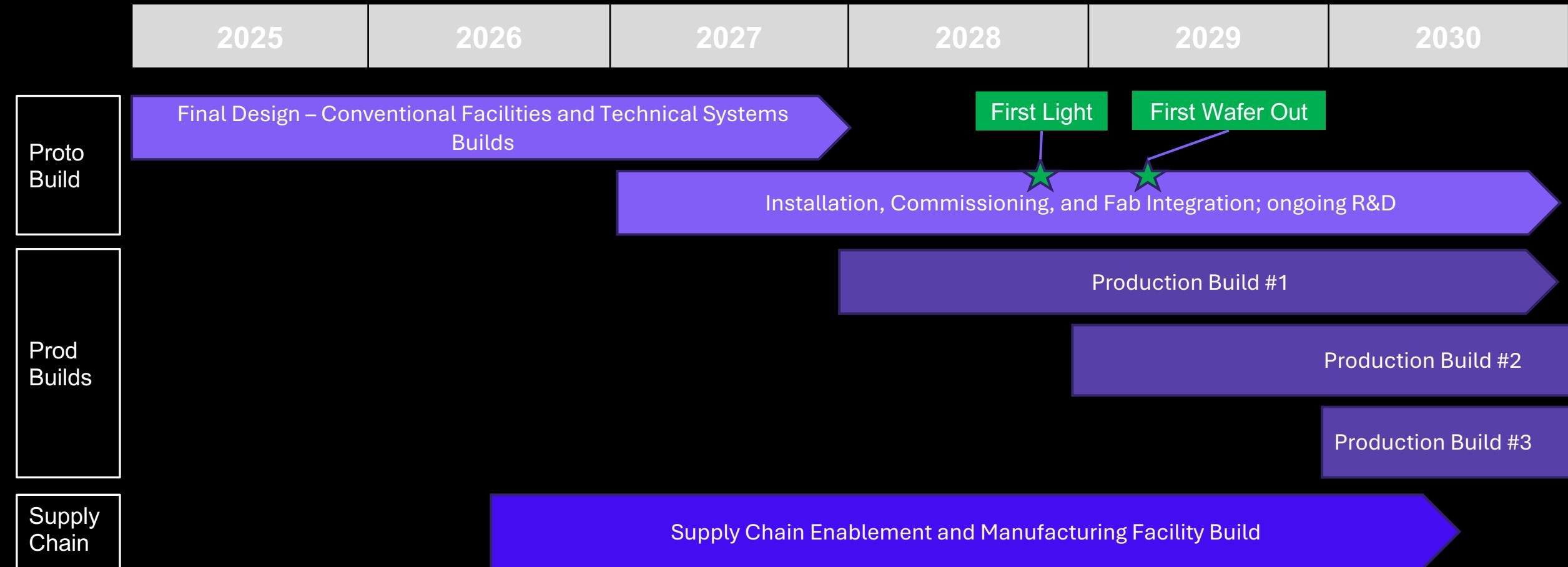
SLAC
NATIONAL ACCELERATOR LABORATORY

Building Partnerships and Prototype Now



- Horizontal Reflection
- Vertical Reflection
- Compound Reflection
- Ground Penetration
- Underground

Roadmap



xLight